

**GLASS PASSIVATED SUPER FAST  
SILICON SURFACE MOUNT BRIDGE RECTIFIER**  
**VOLTAGE RANGE 50 to 400 Volts CURRENT 1.0 Ampere**

**FEATURES**

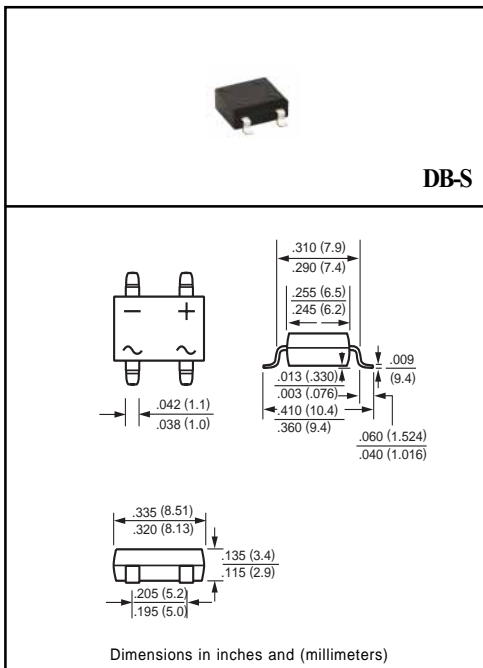
- \* Surge overloading rating - 50 amperes peak
- \* Ideal for printed circuit board
- \* Reliable low cost construction utilizing molded
- \* Glass passivated device
- \* Polarity symbols molded on body
- \* Mounting position: Any
- \* Weight: 1.0 gram

**MECHANICAL DATA**

- \* Epoxy : Device has UL flammability classification 94V-0

**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

Ratings at 25 °C ambient temperature unless otherwise specified.  
Single phase, half wave, 60 Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.



**MAXIMUM RATINGS** (At TA = 25°C unless otherwise noted)

RATINGS	SYMBOL	EDB101S	EDB102S	EDB103S	EDB104S	EDB105S	EDB106S	UNITS
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	50	100	150	200	300	400	Volts
Maximum RMS Volts	V <sub>RMS</sub>	35	70	105	140	210	280	Volts
Maximum DC Blocking Voltage	V <sub>DC</sub>	50	100	150	200	300	400	Volts
Maximum Average Forward Current at TA = 55°C	I <sub>O</sub>	1.0						Amps
Peak Forward Surge Current I <sub>FM</sub> (surge): 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	I <sub>FSM</sub>	30						Amps
Typical Junction Capacitance (Note 2)	C <sub>J</sub>	15				10		pF
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to + 150						°C

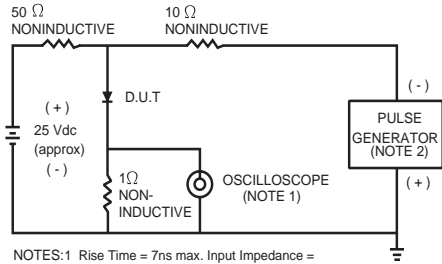
**ELECTRICAL CHARACTERISTICS** (At TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	EDB101S	EDB102S	EDB103S	EDB104S	EDB105S	EDB106S	UNITS
Maximum Forward Voltage at 1.0A DC	V <sub>F</sub>	1.0				1.25		Volts
Maximum DC Reverse Current	I <sub>R</sub>	5.0				50		uAmps
at Rated DC Blocking Voltage								
Maximum Reverse Recovery Time (Note 1)	t <sub>rr</sub>	50						nSec

NOTES : 1. Test Conditions: I<sub>F</sub>=0.5A, I<sub>R</sub>=-1.0A, I<sub>RR</sub>=-0.25A.  
2. Measured at 1 MHz and applied reverse voltage of 4.0 volts.

# RATING AND CHARACTERISTIC CURVES ( EDB101S THRU EDB106S )

FIG. 1 - TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC



NOTES: 1. Rise Time = 7ns max. Input Impedance = 1 megohm, 22 pF.  
2. Rise Time = 10ns max. Source Impedance = 50 ohms.

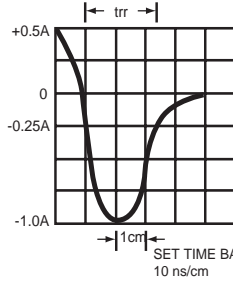


FIG. 2 - TYPICAL FORWARD CURRENT DERATING CURVE

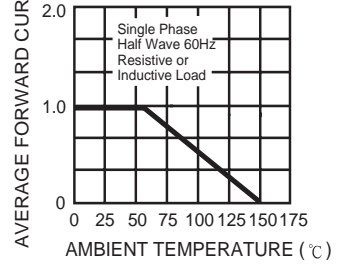


FIG. 3 - TYPICAL REVERSE CHARACTERISTICS

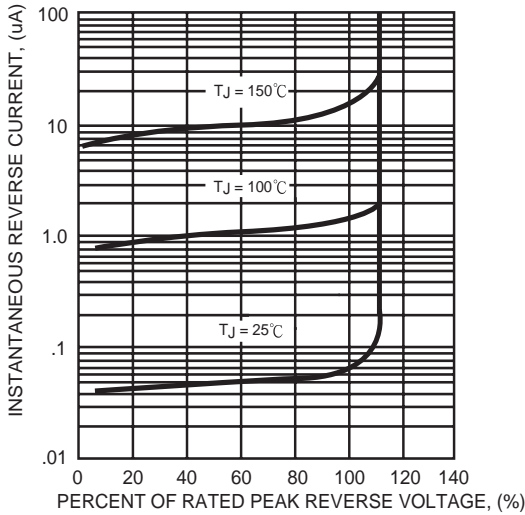


FIG. 4 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

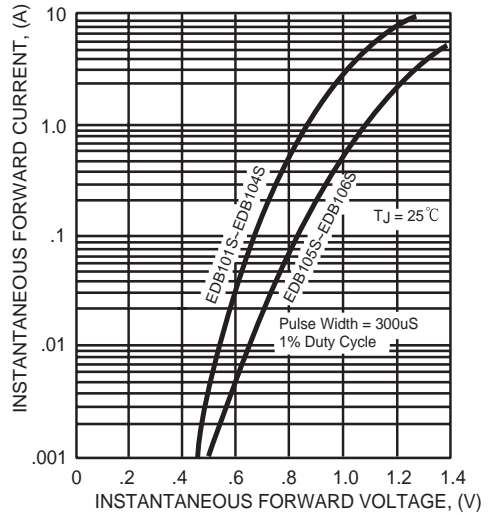


FIG. 5 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

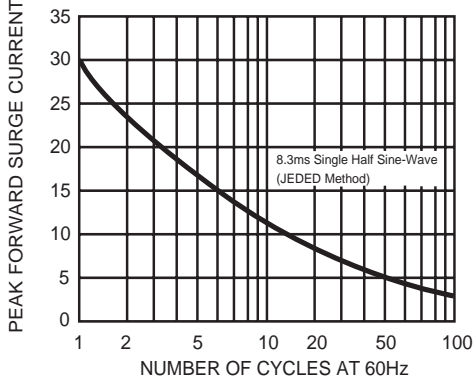


FIG. 6 - TYPICAL JUNCTION CAPACITANCE

